New Jersey Semi-Conductor Products, Inc. TELEPHONE: (973) 376-2922 20 STERN AVE. SPRINGFIELD, NEW JERSEY 07081 (212) 227-6005 U.S.A. FAX: (973) 376-8960 **MRF555 RF & MICROWAVE DISCRETE** LOW POWER TRANSISTORS Features ٠ Specified @ 12.5 V, 470 MHz Characteristics Output Power = 1.5 W Minimum Gain = 11 dB

- Efficiency 60% (Typ)
- Cost Effective PowerMacro Package
- Electroless Tin Plated Leads for Improved Solderability

**Power Macro** 

**DESCRIPTION:** Designed primarily for wideband large signal stages in the UHF frequency range.

### **ABSOLUTE MAXIMUM RATINGS** (Tcase = $25^{\circ}$ C)

Symbol	Parameter	Value	Unit	
V <sub>CEO</sub>	Collector-Emitter Voltage	16	Vdc	
V <sub>CBO</sub>	Collector-Base Voltage	30	Vdc	
V <sub>EBO</sub>	Emitter-Base Voltage	3.0	Vdc	
lc	Collector Current	500	mA	

#### **Thermal Data**

P	Total Device Dissipation @ TC = 75°C	3.0	Watts
D	Derate above 75°C	40	mW/ º <b>C</b>
		40	

NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

## Quality Semi-Conductors

# ELECTRICAL SPECIFICATIONS (Tcase = $25^{\circ}$ C)

### STATIC

Symbol	Test Conditions		Value		
		Min.	Тур.	Max.	Unit
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage ( $I_c = 5 \text{ mAdc}, I_B = 0$ )	16	-	-	Vdc
BV <sub>CES</sub>	Collector-Emitter Sustaining Voltage ( $I_c = 5.0$ mAdc, $I_B = 0$ )	30	-	-	Vdc
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage $(I_E = 0.1 \text{ mAdc}, I_C = 0)$	3.0	-	-	Vdc
Ices	Collector Cutoff Current ( $V_{CE} = 15 \text{ Vdc}, V_{BE} = 0 \text{ Vdc}$ )	-	-	5	mA
HFE	DC Current Gain ( $I_c = 100 \text{ mA}, V_{cE} = 5.0 \text{ Vdc}$ ) Both	50	-	200	-

### DYNAMIC

Symbol	Test Conditions	Value			
		Min.	Тур.	Max.	Unit
Сов	Output Capacitance (VCB = 10 Vdc, IE = 0, f = 1.0 MHz)	-		5.5	pF

### FUNCTIONAL

Symbol	Test C	onditions		Value		
			Min.	Min. Typ.		Unit
G <sub>PE</sub>	Power Gain	Test Circuit-Figure 1 Pout = 1.5 W, VCE =12.5Vdc f = 470 MHz	11	12.5	-	dB
η	Collector Efficiency	Test Circuit-Figure 1 Pout = 1.5 W, VCE =12.5Vdc f = 175 MHz	50	60	-	%
Ψ	Load Mismatch VSWR ≥ 10:1 All Phase Angles	Test Circuit-Figure 1 Pout = 1.5 W, VCE =12.5Vdc f = 175 MHz	No Degradation in Output Power			-